

PRO
11046 U.S.
10/083611
02/27/02

P

PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10083611	02/27/2002	257	316	2812	BOSTON

**APPLICANTS: Hisamune Yoshiaki; Nakata Hidetoshi;

**CONTINUING DATA VERIFIED:

THIS APPLICATION IS A DIV OF 09/489,332 01/21/2000 PAT 6,373,096

BEST AVAILABLE COPY

** FOREIGN APPLICATIONS VERIFIED:

JAPAN 11-014707 01/22/1999

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>	
Foreign priority claimed 35 USC 119 conditions met	<input type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> yes <input type="checkbox"/> no	ATTORNEY DOCKET NO 8020-1002-1	
Verified and Acknowledged Examiners's initials			
TITLE : Method of manufacturing semiconductor device, nonvolatile semiconductor memory device and method of manufacturing the same			
U.S.DEP.T. OF COMM./PAT. & TM-PTO-436L(Rev. 12-94)			

NOTICE OF ALLOWANCE MAILED		Assistant Examiner	CLAIMS ALLOWED	
			Total Claims	Print Claim for O.G.
ISSUE FEE		DRAWING		
Amount Due	Date Paid	Sheets Drwg.		Figs.Drwg.
				Print Fig.
		Primary Examiner		
<input type="checkbox"/> TERMINAL DISCLAIMER		PREPARED FOR ISSUE		Application Examiner
WARNING: The information disclosed herein may be restricted. Unauthorized disclosure may be prohibited by the United States Code Title 35, Sections 122, 181 and 368. Possession outside the U.S. Patent & Trademark Office is restricted to authorized employees and contractors only.				

FILED WITH: DISK (CRF) CD-ROM
(Attached in pocket on right inside flap)